

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1-17 (Canceled)

Claim 18 (Currently Amended): A non-volatile memory array having vertical transistors, wherein at least one each of the vertical transistors is formed in a trench of a semiconductor substrate and comprises:

a first doping region of a first conductive type being underneath [[the]] a bottom of the trench;

a second doping region of the first conductive type being beside [[the]] a top of the trench;

a third doping region of a second conductive type beside the trench;

a fourth doping region of the first conductive type beside the trench, and being located lower than the third doping region;

a gate dielectric layer formed on the first doping region, the second doping region and [[the]] a sidewall of the trench, wherein the gate dielectric layer comprises at least

one nitride film; and

a conducting plug formed in the trench,

wherein the first doping regions of the vertical transistors are connected as a common plate serving as one of a common source and a common drain.

Claim 19 (Original): The non-volatile memory array having vertical transistors of Claim 18, wherein the semiconductor substrate is constituted of a silicon substrate and a mask layer.

Claim 20 (Original): The non-volatile memory array having vertical transistors of Claim 19, wherein the mask layer is selected from the group of silicon nitride, silicon oxide, silicon oxynitride and multi-layer thereof.

Claim 21 (Original): The non-volatile memory array having vertical transistors of Claim 19, wherein the mask layer is of a thickness between 100 to 2000 angstroms.

Claim 22 (Currently Amended): The non-volatile memory array having vertical transistors of Claim 18, wherein the first and second doping regions ~~functions~~ function

as bit lines for the non-volatile memory array.

Claim 23 (Original): The non-volatile memory array having vertical transistors of Claim 18, wherein the gate dielectric layer is an oxide/nitride/oxide layer.

Claim 24 (Original): The non-volatile memory array having vertical transistors of Claim 23, wherein the oxide/nitride/oxide layer is of a thickness between 60-500 angstroms.

Claim 25 (Currently Amended): The non-volatile memory array having vertical transistors of Claim 18, wherein the conducting ~~plugs are plug is a polysilicon~~ [[plugs]] plug.

Claim 26 (Currently Amended): The non-volatile memory array having vertical transistors of Claim 18, wherein the at least one of the vertical transistors further comprises insulation blocks formed on [[the]] surfaces of the first and second doping regions.

Claim 27 (Currently Amended): The non-volatile memory array having vertical transistors of Claim 26, wherein the at least one of the vertical transistors further comprises edge insulation layers formed on sidewalls of the trench trenches, and the insulation blocks are thicker than the edge insulation layers.

Claims 28-32 (Canceled)